ABSTRACT OF THE DISCLOSURE

    A mask pattern correction method includes the step
of extracting a correction target edge from a design
pattern, the step of calculating the distance from
the correction target edge to the nearest edge of
an adjacent pattern, the step of calculating the
correction value by a simulation in accordance with a
pattern layout present within a given range determined
by the correction target edge, and moving the
correction target edge on the basis of the calculated
correction value when the distance calculated in the
distance calculation step is smaller than a predeter-
mined distance, and the step of moving the correction
target edge on the basis of an correction value set as
a rule in advance in accordance with the distance when
the distance calculated in the distance calculation
step is larger than the predetermined distance.